

Appl. No. 09/480,973

REMARKS

Claims 1-9 and 18 are cancelled, claim 10 is amended, and claims 10-17 and 19-37 are pending in the application. The amendment to claim 10 comprises incorporation of the subject matter of previous claim 10 into claim 10, and therefore does not introduce "new matter" into claim 10. Applicant requests substantive examination of the pending claims.

Respectfully submitted,

Dated: MARCH 6, 2002By: 

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Inventor Chris Parfeniuk et al.
Assignee Honeywell International Inc.
Group Art Unit 2823
Examiner D. Collins
Attorney's Docket No. 30-5016-(4015)
Title: Methods of Bonding Physical Vapor Deposition Target Materials to Backing Plate
Materials

**VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
SUPPLEMENTAL AMENDMENT**

In the Specification

The replacement specification paragraphs incorporate the following amendments.

Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The title has been amended as follows:

~~Methods of Bonding First and Second Masses to One Another, and Methods of~~
Bonding Physical Vapor Deposition Target Materials to Backing Plate Materials

In the Claims

The claims have been amended as follows. Underlines indicate insertions and
~~strikeouts~~ indicate deletions.

Cancel claims 1-9 and 18.

10. (amended) A method of bonding a physical vapor deposition target
material to a backing plate material, comprising:

joining the target material and backing plate material in physical contact with one

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another, the backing plate and target material both predominately comprising aluminum; and

thermally treating the joined target and backing plate materials to simultaneously diffusion bond the target material to the backing plate material and develop grains in the target material, the diffusion bonding comprising solid state diffusion between the backing plate and target materials, a predominate portion of the developed grains having a maximum dimension of less than 100 microns.